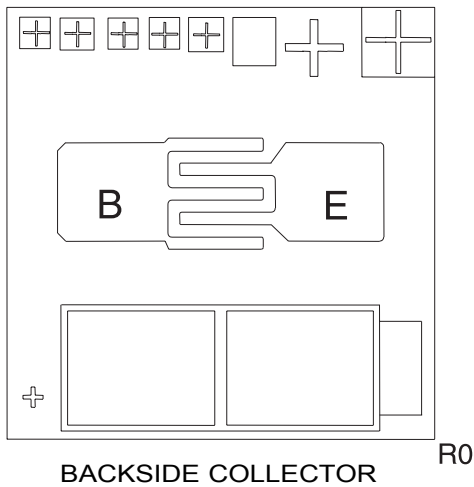


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	14.5 x 14.5 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	2.4 x 2.2 MILS
Emitter Bonding Pad Area	2.4 x 2.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

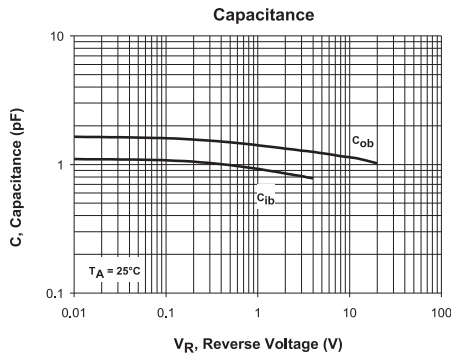
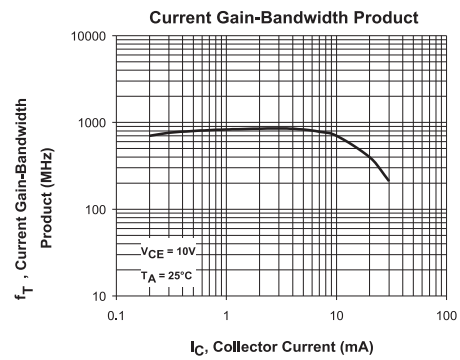
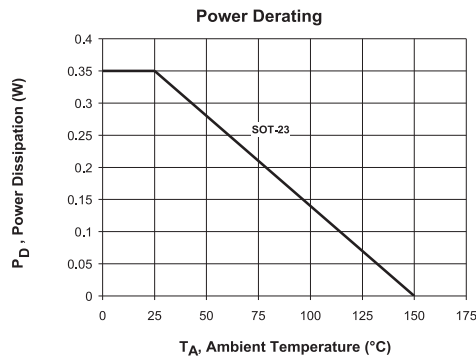
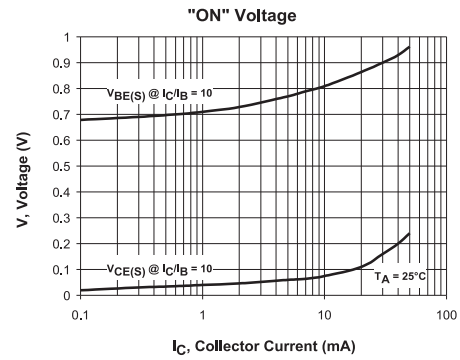
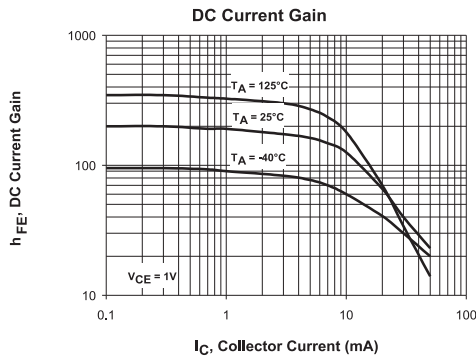
53,730

**PRINCIPAL DEVICE TYPES**

CMPT918  
2N918  
2N2857  
2N5179  
2N5770  
BFY90  
PN3563  
PN3564

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